HIGH-SPEED 3.3V 32K x 36 SYNCHRONOUS PIPELINED DUAL-PORT STATIC RAM WITH 3.3V OR 2.5V INTERFACE

70V3579S

Features:

- True Dual-Port memory cells which allow simultaneous access of the same memory location
- High-speed clock to data access
- Commercial: 4.2/5/6ns (max.)
- Industrial: 5ns (max)
- Pipelined output mode
- Counter enable and reset features
- Dual chip enables allow for depth expansion without additional logic
- Full synchronous operation on both ports
 - 7.5ns cycle time, 133MHz operation (9.6 Gbps bandwidth)
 - Fast 4.2ns clock to data out
 - 1.8ns setup to clock and 0.7ns hold on all control, data, and address inputs @ 133MHz

- Data input, address, byte enable and control registers
- Self-timed write allows fast cycle time
- Separate byte controls for multiplexed bus and bus matching compatibility
- LVTTL- compatible, single 3.3V (±150mV) power supply for core
- LVTTL compatible, selectable 3.3V (±150mV)/2.5V (±125mV) power supply for I/Os and control signals on each port
- Industrial temperature range (-40°C to +85°C) is available for selected speeds
- Available in a 208-pin Plastic Quad Flatpack (PQFP) and 208-pin fine pitch Ball Grid Array, and 256-pin Ball Grid Array
- * Green parts available, see ordering information



AUGUST 2019

Functional Block Diagram

70V3579S High-Speed 32K x 36 Dual-Port Synchronous Pipelined Static RAM

Industrial and Commercial Temperature Ranges

Description:

The IDT70V3579 is a high-speed 32K x 36 bit synchronous Dual-Port RAM. The memory array utilizes Dual-Port memory cells to allow simultaneous access of any address from both ports. Registers on control, data, and address inputs provide minimal setup and hold times. The timing latitude provided by this approach allows systems to be designed with very short cycle times. With an input data register, the IDT70V3579 has been optimized for applications having unidirectional or bidirectional data flow in bursts. An automatic power down feature, controlled by \overline{CE}_0 and CE1, permits the on-chip circuitry of each port to enter a very low standby power mode.

The 70V3579 can support an operating voltage of either 3.3V or 2.5V on one or both ports, controllable by the OPT pins. The power supply for the core of the device (VDD) remains at 3.3V.

A1 IO19L	A2 IO18L	A3 Vss	A4 NC	A5 NC	A6 NC	A7 A12L	A8 A8L	A9 BE1L	A10 Vdd	A11 CLKL	A12 CNTENL	A13 A4L	A14 AoL	A15 OPTL	A16 I/O17L	A17 Vss
B1 I/O20R	^{B2} Vss	b3 I/O18R	^{B4} Vss	^{B5} NC	B6 A13L	B7 A9L	b8 BE2l	B9 CE0L	^{B10} Vss	^{B11} ADSL	B12 A5L	B13 A1L	^{B14} Vss	^{b15} Vddqr	в16 I/O16L	^{B17} I/O15R
C1 Vddql	C2 I/O19R	c3 Vddqr	C4 Vdd	C5 NC	C6 A14L	C7 A10L	C8 BE3L	C9 CE1L	C10 Vss	C11 R/WL	C12 A6L	C13 A2L	C14 VDD	C15 I/O16R	C16 I/O15L	C17 Vss
D1 I/O22L	D2 Vss	d3 I/O21L	d4 I/O20l	D5 NC	D6 A11L	D7 A7L	d8 BEol	d9 Vdd	D10 OEL	D 1 1 CNTRSTL	D12 A3L	D13 Vdd	D14 I/O17R	d15 Vddql	d16 I/O14L	D17 I/O14R
e1 I/O23l	e2 I/O22r	e3 Vddqr	e4 I/O21R										E14 I/O12L	E15 I/O13R	E16 VSS	e17 I/O13l
f1 Vddql	f2 I/O23R	f3 I/O24L	F4 Vss										F14 Vss	F15 I/O12R	F16 I/O11L	f17 Vddqr
G1 I/O26L	_{G2} Vss	G3 I/O25L	G4 I/O24R				70		70				G14 I/O9L	g15 Vddql	G16 I/O10L	G17 I/O11R
H1 Vdd	h2 I/O26R	h3 Vddqr	h4 I/O25r				Bl)V357 =208	(5)				H14 Vdd	H15 IO9R	H16 Vss	h17 I/O10r
j1 Vddql	j2 Vdd	^{J3} Vss	_{J4} Vss				BF	G208	3(5)				J14 Vss	J15 Vdd	^{J16} Vss	j17 Vddqr
k1 I/O28r	K2 Vss	кз I/O27R	K4 Vss					Pin fp Viev		۱.			к14 I/O7r	k15 Vddql	K16 I/O8r	K17 Vss
l1 I/O29R	l2 I/O28L	l3 Vddqr	l4 I/O27l				- 1-						l14 I/O6r	l15 I/O7l	L16 Vss	l17 I/O8l
M1 Vddql	m2 I/O29L	m3 I/O30r	^{M4} Vss										M14 Vss	M15 I/O6l	^{m16} I/O5r	^{M17} Vddqr
N1 I/O31L	N2 Vss	n3 I/O31r	n4 I/O30l										n14 I/O3r	n15 Vddql	N16 I/O4r	n17 I/O5l
P1 I/O32R	p2 I/O32l	p3 Vddqr	p4 I/O35r	P5 NC	P6 NC	P7 A12R	P8 A8R	P9 BE1R	P10 Vdd	P11 CLKr	P12 CNTEN	P13 A 4R	P14 I/O2L	p15 I/O3l	P16 Vss	P17 I/O4L
R1 Vss	r2 I/O33l	r3 I/O34r	^{R4} NC	^{R5} NC	R6 A13R	R7 A9R	r8 BE2r	r9 CE0r	R10 Vss	^{R11} ADSr	R12 A5R	R13 A1R	R14 Vss	r15 Vddql	r16 I/O1r	r17 Vddqr
t1 I/O33r	t2 I/O34l	t3 Vddql	^{T4} Vss	T5 NC	t6 A14R	T7 A10R	t8 BE3r	^{T9} CE1R	T10 Vss	t11 R/Wr	T12 A 6R	T13 A 2R	^{T14} Vss	t15 I/Oor	^{T16} Vss	t17 I/O2r
U1 Vss	u2 I/O35l	U3 Vdd	U4 NC	^{U5} NC	U6 A11R	U7 A7R	u8 BEor	u9 Vdd	U10 OER	U11 CNTRSTR	U12 Азк	U13 Aor	U14 Vdd	U15 OPTR	U16 I/Ool	U17 I/O1L

Pin Configuration^(1,2,3,4)

4830 drw 02c

- 1. All VDD pins must be connected to 3.3V power supply.
- 2. All VDDo pins must be connected to appropriate power supply: 3.3V if OPT pin for that port is set to VIH (3.3V), and 2.5V if OPT pin for that port is set to VIL (0V).
- 3. All Vss pins must be connected to ground supply.
- 4. Package body is approximately 15mm x 15mm x 1.4mm, with 0.8mm ball-pitch.
- 5. This package code is used to reference the package diagram.
- 6. This text does not indicate orientation of the actual part-marking.

70V3579S High-Speed 32K x 36 Dual-Port Synchronous Pipelined Static RAM

Pin Configuration^(1,2,3,4) (con't.)

70V3579 BC256⁽⁵⁾ BCG256⁽⁵⁾

256-Pin BGA Top View⁽⁶⁾

A1	A2	A3	A4	A5	A6	A7	A8	A9	A10	A11	A12	A13	A14	A15	A16
NC	NC	NC	NC	A14L	A11L	A8L	BE2L	CE1L	OEL	CNTENL	A5L	A2L	A0L	NC	NC
b1 I/O18L	^{B2} NC	^{B3} NC	^{B4} NC	^{B5} NC	B6 A12L	B7 A9L	B8 BE3L	B9 CE0L	^{B10} R∕₩L	B 1 1 CNTRSTL	B12 A4L	B13 A1L	B14 Vdd	в15 I/O17L	^{B16} NC
C1	C2	C3	C4	C5	C6	C7	C8	C9	C10	C11	C12	C13	C14	C15	C16
I/O18R	I/O19L	Vss	NC	A13L	A10L	A7L	BE1L	BE0L	CLKL	ADSL	A6L	A3L	OPTL	I/O17R	I/O16L
D1	d2	d3	d4	d5	d6	d7	d8	d9	d10	d11	d12	d13	D14	D15	D16
I/O20R	I/O19r	I/O20l	Vdd	Vddql	Vddql	Vddqr	Vddqr	Vddql	Vddql	Vddqr	Vddqr	Vdd	I/O15R	I/O15L	I/O16R
e1	e2	e3	e4	e5	e6	E7	^{E8}	^{E9}	E10	e11	e12	e13	Е14	e15	e16
I/O21r	I/O21l	I/O22l	Vddql	Vdd	Vdd	VSS	Vss	Vss	Vss	Vdd	Vdd	Vddqr	I/O13L	I/O14L	I/O14r
F1	f2	f3	f4	f5	F6	F7	F8	^{F9}	F10	F11	F12	f13	F14	F15	F16
I/O23L	I/O22R	I/O23r	Vddql	Vdd	Vss	Vss	Vss	Vss	Vss	Vss	Vdd	Vddqr	I/O12R	I/O13R	I/O12L
G1	g2	G3	g4	G5	G6	G7	G8	^{G9}	G10	G11	G12	g13	G14	G15	G16
I/O24R	I/O24L	I/O25L	Vddqr	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vddql	I/O10L	I/O11L	I/O11R
h1	h2	h3	h4	H5	H6	^{H7}	H8	H9	H10	H11	H12	h13	h14	H15	h16
I/O26l	I/O25R	I/O26r	Vddqr	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vddql	I/O9r	IO9∟	I/O10R
J1	j2	j3	j4	_{J5}	^{J6}	_{J7}	_{J8}	^{J9}	J10	J11	J12	j13	J14	j15	J16
I/O27L	I/O28R	I/O27R	Vddql	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vddqr	I/O8r	I/O7r	I/O8L
K1	k2	k3	k4	K5	K6	к7	K8	к9	K10	K11	K12	k13	k14	k15	K16
I/O29R	I/O29l	I/O28L	Vddql	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vss	Vddqr	I/O6r	I/O6l	I/O7l
l1	l2	l3	l4	l5	L6	L7	L8	L9	L10	L11	l12	l13	l14	l15	l16
I/O30l	I/O31R	I/O30r	Vddqr	Vdd	Vss	Vss	Vss	Vss	Vss	Vss	Vdd	Vddql	I/O5l	I/O4r	I/O5r
m1	m2	мз	^{m4}	^{M5}	M6	M7	^{M8}	M9	M10	M11	M12	m13	m14	m15	^{M16}
I/O32R	I/O32l	I/Oз1l	Vddqr	Vdd	Vdd	Vss	Vss	Vss	Vss	Vdd	Vdd	Vddql	I/O3r	I/O3l	I/O4L
n1	n2	n3	N4	n5	n6	n7	n8	n9	n10	n11	n12	N13	N14	^{N15}	n16
I/O33l	I/O34r	I/O33r	Vdd	Vddqr	Vddqr	Vddql	Vddql	Vddqr	Vddqr	Vddql	Vddql	Vdd	I/O2L	I/O1r	I/O2r
P1	p2	P3	P4	P5	P6	P7	P8	P9	P10	^{P11}	P12	P13	P14	p15	p16
I/O35R	I/O34L	NC	NC	A13R	A10R	A7R	BE1R	BE0r	CLKR	ADSr	A6R	A3R	I/Ool	I/Oor	I/O1l
r1	^{R2}	^{R3} NC	^{R4}	^{R5}	R6	R7	R8	R9	R10	r11	R12	R13	^{R14}	R15	R16
I/O35L	NC		NC	NC	A12R	A9R	BE3R	CE0R	R/W R	CNTRSTR	A4R	A1R	OPTr	NC	NC
T1	T2	T3	T4	T5	т6	t7	t8	^{T9}	T10	t11	T12	T13	T14	T15	^{T16} NC
NC	NC	NC	NC	A 14R	А 11R	A8R	BE2r	CE1R	OEr	CNTENR	A 5R	A 2R	A 0R	NC	

4830 drw 02d

- 1. All VDD pins must be connected to 3.3V power supply.
- 2. All VDDo pins must be connected to appropriate power supply: 3.3V if OPT pin for that port is set to VIH (3.3V), and 2.5V if OPT pin for that port is set to VIL (0V).
- 3. All Vss pins must be connected to ground supply.
- 4. Package body is approximately 17mm x 17mm x 1.4mm, with 1.0mm ball-pitch.
- 5. This package code is used to reference the package diagram.
- 6. This text does not indicate orientation of the actual part-marking.



- 1. All VDD pins must be connected to 3.3V power supply.
- 2. All VDDQ pins must be connected to appropriate power supply: 3.3V if OPT pin for that port is set to VIH (3.3V), and 2.5V if OPT pin for that port is set to VIL (0V).
- 3. All Vss pins must be connected to ground supply.
- 4. Package body is approximately 28mm x 28mm x 3.5mm.
- 5. This package code is used to reference the package diagram.

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Pin Names

Left Port	Right Port	Names
CE OL, CE1L	CEOR, CE1R	Chip Enables
R/WL	R/WR	Read/Write Enable
OEL	OE R	Output Enable
A0l - A14l	A0R - A14R	Address
1/Ool - 1/O35l	1/Oor - 1/O35r	Data Input/Output
CLKL	CLKr	Clock
ADSL	ADS R	Address Strobe Enable
<u>CNTEN</u> L		Counter Enable
	CNTRST R	Counter Reset
BEOL - BE3L	BEOR - BE3R	Byte Enables (9-bit bytes)
VDDQL	Vddqr	Power (I/O Bus) (3.3V or 2.5V) ⁽¹⁾
OPTL	OPTR	Option for selecting VDDax ^(1,2)
	Vdd	Power (3.3V) ⁽¹⁾
	Vss	Ground (0V)

Industrial and Commercial Temperature Ranges

NOTES:

- 1. VDD, OPTx, and VDDox must be set to appropriate operating levels prior to applying inputs on the I/Os and controls for that port.
- 2. OPTx selects the operating voltage levels on that port. If OPTx is set to VIH (3.3V), then that port's I/Os and controls will operate at 3.3V levels and VDDOX must be supplied at 3.3V. If OPTx is set to VIL (0V), then that port's I/Os and controls will operate at 2.5V levels and VDDox must be supplied at 2.5V. The OPT pins are independent of one another-both ports can operate at 3.3V levels, both can operate at 2.5V levels, or either can operate at 3.3V with the other at 2.5V.

Truth Table I—Read/Write and Enable Control^(1,2,3,4)

ŌĒ	CLK	Ē	CE1	ΒĒ₃	BE2	BE 1	BE 0	R/W	Byte 3 I/O27-35	Byte 2 I/O18-26	Byte 1 I/O9-17	Byte 0 I/Oo-8	MODE
Х	\uparrow	Н	Х	Х	Х	Х	Х	Х	High-Z	High-Z	High-Z	High-Z	Deselected–Power Down
Х	Ŷ	Х	L	Х	Х	Х	Х	Х	High-Z	High-Z	High-Z	High-Z	Deselected–Power Down
Х	\uparrow	L	Н	Н	Н	Н	Н	Х	High-Z	High-Z	High-Z	High-Z	All Bytes Deselected
Х	\uparrow	L	Н	Н	Н	Н	L	L	High-Z	High-Z	High-Z	Din	Write to Byte 0 Only
Х	Ŷ	L	Н	Н	Н	L	Н	L	High-Z	High-Z	Din	High-Z	Write to Byte 1 Only
Х	Ŷ	L	Н	Н	L	Н	Н	L	High-Z	Din	High-Z	High-Z	Write to Byte 2 Only
Х	\uparrow	L	Н	L	Н	Н	Н	L	Din	High-Z	High-Z	High-Z	Write to Byte 3 Only
Х	Ŷ	L	Н	Н	Н	L	L	L	High-Z	High-Z	Din	Din	Write to Lower 2 Bytes Only
Х	\uparrow	L	Н	L	L	Н	Н	L	Din	Din	High-Z	High-Z	Write to Upper 2 bytes Only
Х	Ŷ	L	Н	L	L	L	L	L	Din	Din	Din	Din	Write to All Bytes
L	\uparrow	L	Н	Н	Н	Н	L	Н	High-Z	High-Z	High-Z	Dout	Read Byte 0 Only
L	\uparrow	L	Н	Н	Н	L	Н	Н	High-Z	High-Z	Dout	High-Z	Read Byte 1 Only
L	Ŷ	L	Н	Н	L	Н	Н	Н	High-Z	Dout	High-Z	High-Z	Read Byte 2 Only
L	\uparrow	L	Н	L	Н	Н	Н	Н	Dout	High-Z	High-Z	High-Z	Read Byte 3 Only
L	\uparrow	L	Н	Н	Н	L	L	Н	High-Z	High-Z	Dout	Dout	Read Lower 2 Bytes Only
L	\uparrow	L	Н	L	L	Н	Н	Н	Dout	Dout	High-Z	High-Z	Read Upper 2 Bytes Only
L	\uparrow	L	Н	L	L	L	L	Н	Dout	Dout	Dout	Dout	Read All Bytes
Н	↑	L	Н	L	L	L	L	Х	High-Z	High-Z	High-Z	High-Z	Outputs Disabled

1. "H" = VIH, "L" = VIL, "X" = Don't Care.

2. \overline{ADS} , \overline{CNTEN} , $\overline{CNTRST} = X$.

3. OE is an asynchronous input signal.

4. It is possible to read or write any combination of bytes during a given access. A few representative samples have been illustrated here.

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Industrial and Commercial Temperature Ranges

Truth Table II—Address Counter Control^(1,2)

Address	Previous Address	Addr Used	CLK ⁽⁶⁾	ADS	CNTEN	CNTRST	I/O ⁽³⁾	MODE
Х	Х	0	\uparrow	Х	Х	L ⁽⁴⁾	Dvo(0)	Counter Reset to Address 0
An	Х	An	\uparrow	L ⁽⁴⁾	Х	Н	Dvo (n)	External Address Used
An	Ар	Ар	Ŷ	Н	Н	Н	Dvo(p)	External Address Blocked—Counter disabled (Ap reused)
Х	Ар	Ap + 1	Ŷ	Н	L ⁽⁵⁾	Н	Dvo(p+1)	Counter Enabled—Internal Address generation
								4830 tbl 03

NOTES:

1. "H" = VIH, "L" = VIL, "X" = Don't Care.

2. Read and write operations are controlled by the appropriate setting of R/W, CE0, CE1, BEn and OE.

3. Outputs are in Pipelined mode: the data out will be delayed by one cycle.

4. ADS and CNTRST are independent of all other memory control signals including CEo, CE1 and BEn

5. The address counter advances if CNTEN = VIL on the rising edge of CLK, regardless of all other memory control signals including CE0, CE1, BEn.

Recommended Operating Temperature and Supply Voltage⁽¹⁾

Grade	Ambient Temperature	GND	Vdd
Commercial	0°C to +70°C	0V	3.3V <u>+</u> 150mV
Industrial	-40°C to +85°C	0V	3.3V <u>+</u> 150mV
			4830 tbl 04

NOTE:

 Industrial temperature: for specific speeds, packages and powers contact your sales office.

Absolute Maximum Ratings⁽¹⁾

Symbol	Rating	Commercial & Industrial	Unit
Vterm ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +4.6	V
Tbias	Temperature Under Bias	-55 to +125	٥C
Tstg	Storage Temperature	-65 to +150	٥C
Іоит	DC Output Current	50	mA
			4830 tbl 06

NOTES:

 Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

 VTERM must not exceed VDD + 150mV for more than 25% of the cycle time or 4ns maximum, and is limited to ≤ 20mA for the period of VTERM ≥ VDD + 150mV.

Recommended DC Operating Conditions with VDDQ at 2.5V

Core Supply Voltage	0.45			
-	3.15	3.3	3.45	V
I/O Supply Voltage ⁽³⁾	2.375	2.5	2.625	V
Ground	0	0	0	V
Input High Voltage ⁽³⁾ (Address & Control Inputs)	1.7		Vddq + 125mV ⁽²⁾	V
Input High Voltage - I/O ⁽³⁾	1.7	_	$V_{DDQ} + 125 mV^{(2)}$	V
Input Low Voltage	-0.3(1)	_	0.7	V
	Ground Input High Voltage ⁽³⁾ (Address & Control Inputs) Input High Voltage - <i>VO</i> ⁽³⁾	Ground 0 Input High Voltage ⁽³⁾ 1.7 (Address & Control Inputs) 1.7 Input High Voltage - I/O ⁽³⁾ 1.7	Ground 0 0 Input High Voltage ⁽³⁾ (Address & Control Inputs) 1.7 — Input High Voltage - I/O ⁽³⁾ 1.7 —	Ground 0 0 0 Input High Voltage ⁽³⁾ (Address & Control Inputs) 1.7 — VDDQ + 125mV ⁽²⁾ Input High Voltage - VO ⁽³⁾ 1.7 — VDDQ + 125mV ⁽²⁾

NOTES:

1. VIL \geq -1.5V for pulse width less than 10 ns.

2. VTERM must not exceed VDDQ + 125mV.

 To select operation at 2.5V levels on the I/Os and controls of a given port, the OPT pin for that port must be set to VIL (0V), and VDDOX for that port must be supplied as indicated above.

Symbol	Parameter	Min.	Тур.	Мах.	Unit
Vdd	Core Supply Voltage	3.15	3.3	3.45	V
VDDQ	I/O Supply Voltage ⁽³⁾	3.15	3.3	3.45	V
Vss	Ground	0	0	0	V
V⊪	Input High Voltage (Address & Control Inputs) ⁽³⁾	2.0	_	Vddq + 150mV ⁽²⁾	V
V⊪	Input High Voltage - I/O ⁽³⁾	2.0		VDDQ + 150mV ⁽²⁾	V
Vil	Input Low Voltage	-0.3(1)		0.8	V

Recommended DC Operating Conditions with VDDQ at 3.3V

NOTES:

1. VIL \geq -1.5V for pulse width less than 10 ns.

2. VTERM must not exceed VDDQ + 150mV.

3. To select operation at 3.3V levels on the I/Os and controls of a given port, the OPT pin for that port must be set to VIH (3.3V), and VDDox for that port must be supplied as indicated above.

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Industrial and Commercial Temperature Ranges

Capacitance⁽¹⁾

(TA = +25°C, F = 1.0MHz) PQFP ONLY

Symbol	Parameter	Conditions ⁽²⁾	Max.	Unit
Cin	Input Capacitance	VIN = 3dV	8	рF
Cout ⁽³⁾	Output Capacitance	Vout = 3dV	10.5	рF
10750				4830 tbl 07

NOTES:

1. These parameters are determined by device characterization, but are not production tested.

2. 3dV references the interpolated capacitance when the input and output switch from 0V to 3V or from 3V to 0V.

3. COUT also references CI/O.

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range (VDD = 3.3V ± 150mV)

			70V3	579S	
Symbol	Parameter	Test Conditions	Min.	Max.	Unit
Lu	Input Leakage Current ⁽¹⁾	$V_{DDQ} = Max., V_{IN} = 0V$ to V_{DDQ}	_	10	μA
Ilo	Output Leakage Current	$\overline{CE}_0 = V_{IH} \text{ or } CE_1 = V_{IL}, V_{OUT} = 0V \text{ to } V_{DDQ}$	_	10	μA
Vol (3.3V)	Output Low Voltage ⁽²⁾	Iol = +4mA, VDDQ = Min.	_	0.4	V
Voн (3.3V)	Output High Voltage ⁽²⁾	IOH = -4mA, VDDQ = Min.	2.4	_	V
Vol (2.5V)	Output Low Voltage ⁽²⁾	Iol = +2mA, VDDQ = Min.	_	0.4	V
Vон (2.5V)	Output High Voltage ⁽²⁾	юн = -2mA, Vddq = Min.	2.0	_	V
0750				4	830 tbl 08

NOTES:

1. At VDD \leq - 2.0V input leakages are undefined.

2. VDDQ is selectable (3.3V/2.5V) via OPT pins. Refer to p.4 for details.

70V3579S High-Speed 32K x 36 Dual-Port Synchronous Pipelined Static RAM

Industrial and Commercial Temperature Ranges

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range⁽³⁾ ($VDD = 3.3V \pm 150mV$)

						70V3579S4 Com'l Only		579S5 m'l Ind	70V3579S6 Com'l Only		
ymbol	Parameter	Test Condition	Versio	on	Тур. ⁽⁴⁾	Max.	Тур. ⁽⁴⁾	Max.	Тур. ⁽⁴⁾	Max.	Uni
IDD	Dynamic Operating	CEL and CER= VIL,	COM'L	S	375	460	285	360	245	310	m
	Current (Both Ports Active)	Outputs Disabled, $f = fMAX^{(1)}$	IND	S			285	415	245	360	1
ISB1	Standby Current	$\overline{CE}L = \overline{CE}R = VIH$	COM'L	S	145	190	105	145	95	125	m
	(Both Ports - TTL Level Inputs)	$f = fMAX^{(1)}$	IND	S			105	175	95	150	1
ISB2	Standby Current	\overline{CE} "A" = VIL and \overline{CE} "B" = VIH ⁽⁵⁾	COM'L	S	265	325	190	260	175	225	m
	(One Port - TTL Level Inputs)	Active Port Outputs Disabled, f=fMAX ⁽¹⁾	IND	S		_	190	300	175	260	
ISB3	Full Standby Current (Both Ports - CMOS	Both Ports \overline{CE}_{L} and $\overline{CE}_{R} \ge VDDQ - 0.2V$,	COM'L	S	6	15	6	15	6	15	m
	Level Inputs)	$\label{eq:VIN_second} \begin{array}{l} \text{VIN} \geq \text{VDDQ} - 0.2\text{V} \text{ or VIN} \leq 0.2\text{V}, \\ f = 0^{(2)} \end{array}$	IND	S			6	30	6	30	
ISB4	Full Standby Current (One Port - CMOS Level Inputs)	$\overline{CE}^*A^* \le 0.2V$ and $\overline{CE}^*B^* \ge VDDQ - 0.2V^{(5)}$ VIN > VDDQ - 0.2V or $VIN < 0.2V$,	COM'L	S	265	325	180	260	170	225	m
	Level inputs)	Active Port, Outputs Disabled, $f = fMAX^{(1)}$	IND	S		_	180	300	170	260	

NOTES:

1. At f = fMax, address and control lines (except Output Enable) are cycling at the maximum frequency clock cycle of 1/tcyc, using "AC TEST CONDITIONS" at input levels of GND to 3V.

2. f = 0 means no address, clock, or control lines change. Applies only to input at CMOS level standby.

3. Port "A" may be either left or right port. Port "B" is the opposite from port "A".

4. $V_{DD} = 3.3V$, TA = 25°C for Typ, and are not production tested. IDD DC(f=0) = 120mA (Typ). 5. $\overline{CE}x = V_{IL}$ means $\overline{CE}_{0x} = V_{IL}$ and $CE_{1x} = V_{IH}$

 $\overline{CE}x = VIH$ means $\overline{CE}0x = VIH$ or CE1x = VIL

 $\overline{\text{CE}}x \leq 0.2V$ means $\overline{\text{CE}}\textsc{oss} \leq 0.2V$ and $\text{CE}\textsc{iss} \geq V\textsc{dot}$ - 0.2V

 $\overline{CE} x \geq V \text{DDQ}$ - 0.2V means $\overline{CE} \text{Ox} \geq V \text{DDQ}$ - 0.2V or CE1x - 0.2V

"X" represents "L" for left port or "R" for right port.



Figure 3. Typical Output Derating (Lumped Capacitive Load).

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AC Electrical Characteristics Over the Operating Temperature Range (Read and Write Cycle Timing)^(1,2) (VDD = $3.3V \pm 150$ mV, TA = 0°C to +70°C)

Symbol	Parameter	70V3579S4 Com'l Only		70V3579S5 Com'l & Ind		70V3579S6 Com'l Only		
		Min.	Max.	Min.	Max.	Min.	Max.	Unit
tcyc2	Clock Cycle Time (Pipelined)	7.5	—	10		12	_	ns
tCH2	Clock High Time (Pipelined)	3	—	4		5		ns
tcL2	Clock Low Time (Pipelined)	3	—	4		5		ns
tR	Clock Rise Time	_	3	—	3	—	3	ns
tr	Clock Fall Time	—	3		3	—	3	ns
tsa	Address Setup Time	1.8	—	2.0		2.0	_	ns
tha	Address Hold Time	0.7	—	0.7		1.0	_	ns
tsc	Chip Enable Setup Time	1.8	—	2.0		2.0	_	ns
tнc	Chip Enable Hold Time	0.7	—	0.7		1.0		ns
tsв	Byte Enable Setup Time	1.8	—	2.0		2.0		ns
tHB	Byte Enable Hold Time	0.7	—	0.7	—	1.0		ns
tsw	R/W Setup Time	1.8	—	2.0	—	2.0		ns
tHW	R/W Hold Time	0.7	—	0.7	—	1.0		ns
tsd	Input Data Setup Time	1.8	—	2.0	—	2.0		ns
thd	Input Data Hold Time	0.7	—	0.7		1.0		ns
tsad	ADS Setup Time	1.8	—	2.0		2.0		ns
thad	ADS Hold Time	0.7	—	0.7		1.0		ns
tscn	CNTEN Setup Time	1.8		2.0		2.0		ns
then	CNTEN Hold Time	0.7		0.7		1.0		ns
t SRST	CNTRST Setup Time	1.8		2.0		2.0		ns
thrst	CNTRST Hold Time	0.7		0.7		1.0		ns
toe ⁽¹⁾	Output Enable to Data Valid	-	4		5	—	6	ns
tolz	Output Enable to Output Low-Z	0		0		0		ns
tонz	Output Enable to Output High-Z	1	4	1	4.5	1	5	ns
tCD2	Clock to Data Valid (Pipelined)		4.2		5	—	6	ns
tDC	Data Output Hold After Clock High	1		1		1		ns
tскнz	Clock High to Output High-Z	1	3	1	4.5	1.5	6	ns
tcklz	Clock High to Output Low-Z	1		1		1		ns
Port-to-Port [Delay	•	•	-	•	•		-
tco	Clock-to-Clock Offset	6		8		10		ns

NOTES:

1. All input signals are synchronous with respect to the clock except for the asynchronous Output Enable (OE).

2. These values are valid for either level of VDD0 (3.3V/2.5V). See page 4 for details on selecting the desired I/O voltage levels for each port.

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Timing Waveform of Read Cycle for Pipelined Operation⁽²⁾



NOTES:

- 1. OE is asynchronously controlled; all other inputs are synchronous to the rising clock edge.
- 2. ADS = VIL, CNTEN and CNTRST = VIH.
- 3. The output is disabled (High-Impedance state) by $\overline{CE}_0 = VIH$, $CE_1 = VIL$, $\overline{BE}_n = VIH$ following the next rising edge of the clock. Refer to Truth Table 1.
- 4. Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 5. If BEn was HIGH, then the appropriate Byte of DATAout for Qn + 2 would be disabled (High-Impedance state).

Timing Waveform of a Multi-Device Pipelined Read^(1,2) CLK A5 Аз A4 A6 ADDRESS(B1) CE0(B1) **t**CKHZ DATAOUT(B1) Q0 Q1 Q3 tDC tDC **t**CKLZ tCKHZ Аз A4 **A**5 A6 ADDRESS(B2) CE0(B2) topa -t<u>CKHZ</u> DATAOUT(B2) Q2 Q4 **t**CKLZ **t**CKLZ 4830 drw 07

NOTES:

1. B1 Represents Device #1; B2 Represents Device #2. Each Device consists of one IDT70V3579 for this waveform,

- and are setup for depth expansion in this example. ADDRESS(B1) = ADDRESS(B2) in this situation.
- 2. BEn, OE, and ADS = VIL; CE1(B1), CE1(B2), R/W, CNTEN, and CNTRST = VIH.

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Timing Waveform of Left Port Write to Pipelined Right Port Read^(1,2)



NOTES:

- 1. \overline{CE}_{0} , \overline{BE}_{n} , and $\overline{ADS} = VIL$; CE1, \overline{CNTEN} , and $\overline{CNTRST} = VIH$.
- 2. $\overline{OE} = V_{IL}$ for the Right Port, which is being read from. $\overline{OE} = V_{IH}$ for the Left Port, which is being written to.
- If tco ≤ minimum specified, then data from right port read is not valid until following right port clock cycle (ie, time from write to valid read on opposite port will be tco + 2 tcyc2 + tcp2). If tco > minimum, then data from right port read is available on first right port clock cycle (ie, time from write to valid read on opposite port will be tco + tcyc2 + tcp2).



NOTES:

- 1. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- 2. CEo, BEn, and ADS = VIL; CE1, CNTEN, and CNTRST = VIH. "NOP" is "No Operation".
- 3. Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 4. "NOP" is "No Operation." Data in memory at the selected address may be corrupted and should be rewritten to guarantee data integrity.

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Timing Waveform of Pipelined Read-to-Write-to-Read (**OE** Controlled)⁽²⁾



NOTES:

- 1. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- 2. CE0, BEn, and ADS = VIL; CE1, CNTEN, and CNTRST = VIH.
- 3. Addresses do not have to be accessed sequentially since ADS = VIL constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 4. This timing does not meet requirements for fastest speed grade. This waveform indicates how logically it could be done if timing so allows.





- 1. \overline{CE}_{0} , \overline{OE} , $\overline{BEn} = V_{IL}$; CE_{1} , R/\overline{W} , and $\overline{CNTRST} = V_{IH}$.
- 2. If there is no address change via $\overline{ADS} = V_{IL}$ (loading a new address) or $\overline{CNTEN} = V_{IL}$ (advancing the address), i.e. $\overline{ADS} = V_{IH}$ and $\overline{CNTEN} = V_{IH}$, then the data output remains constant for subsequent clocks.

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Timing Waveform of Write with Address Counter Advance⁽¹⁾



Timing Waveform of Counter Reset⁽²⁾



NOTES:

1. \overline{CE}_{0} , \overline{BE}_{n} , and $R/\overline{W} = VIL$; CE1 and $\overline{CNTRST} = VIH$.

- 3. The "Internal Address" is equal to the "External Address" when ADS = VIL and equals the counter output when ADS = VIH.
- 4. Addresses do not have to be accessed sequentially since $\overline{ADS} = VIL$ constantly loads the address on the rising edge of the CLK; numbers are for reference use only.
- 5. Output state (High, Low, or High-impedance) is determined by the previous cycle control signals.
- 6. No dead cycle exists during counter reset. A READ or WRITE cycle may be coincidental with the counter reset cycle: ADDR 0 will be accessed. Extra cycles are shown here simply for clarification.
- 7. CNTEN = VIL advances Internal Address from 'An' to 'An +1'. The transition shown indicates the time required for the counter to advance. The 'An +1'Address is written to during this cycle.

^{2.} \overline{CE}_{0} , $\overline{BE}_{n} = VIL$; $CE_{1} = VIH$.

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Functional Description

The IDT70V3579 provides a true synchronous Dual-Port Static RAM interface. Registered inputs provide minimal set-up and hold times on address, data, and all critical control inputs. All internal registers are clocked on the rising edge of the clock signal, however, the self-timed internal write pulse is independent of the LOW to HIGH transition of the clock signal.

An asynchronous output enable is provided to ease asynchronous bus interfacing. Counter enable inputs are also provided to stall the operation of the address counters for fast interleaved memory applications.

A HIGH on \overline{CE} or a LOW on CE1 for one clock cycle will power down the internal circuitry to reduce static power consumption. Multiple chip enables allow easier banking of multiple IDT70V3579s for depth expansion configurations. Two cycles are required with \overline{CE} o LOW and CE1 HIGH to reactivate the outputs.

the and Width Expansion

Industrial and Commercial Temperature Ranges

Depth and Width Expansion

The IDT70V3579 features dual chip enables (refer to Truth Table I) in order to facilitate rapid and simple depth expansion with no requirements for external logic. Figure 4 illustrates how to control the various chip enables in order to expand two devices in depth.

The IDT70V3579 can also be used in applications requiring expanded width, as indicated in Figure 4. Through combining the control signals, the devices can be grouped as necessary to accommodate applications needing 72-bits or wider.



70V3579S High-Speed 32K x 36 Dual-Port Synchronous Pipelined Static RAM Industrial and Commercial Temperature Ranges Ordering Information XXXXX A 999 A A A A Device Power Speed Package Process/ Temperature Bange Process/ Temperature Bange Process/ Temperature



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NOTES:

- 1. Contact your local sales office for additional industrial temp range speeds, packages and powers.
- 2. Green parts available. For specific speeds, packages and powers contact your local sales office. LEAD FINISH (SnPb) parts are Obsolete excluding BGA and fpBGA. Product Discontinuation Notice - PDN# SP-17-02

Note that information regarding recently obsoleted parts are included in this datasheet for customer convenience.

Speed (ns)	Orderable Part ID	Pkg. Code	Pkg. Type	Temp. Grade
4	70V3579S4BC	BC256	CABGA	С
	70V3579S4BC8	BC256	CABGA	С
	70V3579S4BCG	BCG256	CABGA	С
	70V3579S4BF	BF208	CABGA	С
	70V3579S4BF8	BF208	CABGA	С
	70V3579S4BFG	BFG208	CABGA	С
	70V3579S4DRG	DRG208	PQFP	С
5	70V3579S5BC	BC256	CABGA	С
	70V3579S5BC8	BC256	CABGA	С
	70V3579S5BCGI	BCG256	CABGA	I
	70V3579S5BCI	BC256	CABGA	I
	70V3579S5BC18	BC256	CABGA	I
	70V3579S5BF	BF208	CABGA	С
	70V3579S5BF8	BF208	CABGA	С
	70V3579S5BFI	BF208	CABGA	I
	70V3579S5BFI8	BF208	CABGA	I
6	70V3579S6BC	BC256	CABGA	С
	70V3579S6BC8	BC256	CABGA	С
	70V3579S6BCI	BC256	CABGA	I
	70V3579S6BCI8	BC256	CABGA	I
	70V3579S6BF	BF208	CABGA	С
	70V3579S6BF8	BF208	CABGA	С

Orderable Part Information

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Datasheet Document History

12/09/98:	Initial Public Release			
03/12/99:	Added fpBGA package			
04/28/99:	Fixed typo on page 10			
06/08/99:	Changed drawing format			
	Page 2 Changed package body dimensions			
06/15/99:	Page 5 Deleted note 6 for Table II			
08/04/99:	Page 6 Improved power numbers			
10/04/99:	Upgraded speed to 133MHz, added 2.5V I/O capability			
10/19/99:	Page 4 Corrected I/O numbers in Truth Table I			
11/12/99:	Replaced IDT logo			
04/10/00:	Added new BGA package, added full 2.5V interface capability			
01/12/01:	Page 6 Updated Truth Table II			
	Increased storage temperature parameter			
	Clarified TA Parameter			
	Page 8 DC Electrical parameters-changed wording from "open" to "disabled"			
	Removed note 7 on DC Electrical Characteristics table			
	Removed Preliminary status			
04/10/01:	Added Industrial Temperature Ranges and removed related notes			
07/19/01:	Page 3 Replaced incorrect BGA package drawing			
12/12/01:	Page 2, 3 & 4 Added date revision to pin configurations			
	Page 6 Removed industrial temp footnote from table 04			
	Page 8 & 10 Removed industrial temp for 6ns from DC & AC Electrical Characteristics			
	Page 16 Removed industrial temp from 6ns in ordering information			
	Added industrial temp footnote			
	Page 1 & 17 Replaced TM logo with ® logo			
02/07/06:	Page 1 Added green availability to features			
	Page 5 Changed footnote 2 for Truth Table I from ADS, CNTEN, CNTRST = VIH to ADS, CNTEN, CNTRST = X			
	Page 16 Added green indicator to ordering information			
07/25/08:	Page 8 Corrected a typo in the DC Chars table			
10/23/08:	Page 16 Removed "IDT" from orderable part number			
10/10/14:	Page 15 Added Tape and Reel to the Ordering Information			
02/16/18:	Product Discontinuation Notice - PDN# SP-17-02			
	Last time buy expires June 15, 2018			
08/02/19:	Page 2, 3 & 4 Updated package codes BF-208 to BF208, BFG208, DR-208 to DRG208 & BC-256 to BC256 BCG256			
	Page 16 Added Orderable Part Information table			